


6inch 700nm c-cut SiCOI SPEC			
		 4H HPSI (P) SIC 700nm	 Al2O3 1-20nm
		 SiO2 3000nm	 Si 675um
Transfer SIC Layer			
No.	Item	Specification	Remark
1	Poly type	4H	
2	Type	HPSI	
3	Resistivity	$\geq 1E8$ ohm.cm	
4	Orientation	<0001>	
5	off Orientation	$0 \pm 0.25^\circ$	
6	SIC Thickness (19 Pts)	700nm+-100nm	Edge exclusion 8mm
7	Frontside finish	C -face CMP	
8	Frontside Rms-C	$\leq 0.5\text{nm}$ ($5\mu\text{m} * 5\mu\text{m}$)	Edge exclusion 5mm
Modified Layer			
1	Material	Al2O3	
2	Thickness	1-20nm	Process Guarantee
Oxide Layer			
1	Oxide thickness (19 Pts)	3000 $\pm 5\%$ nm	Edge exclusion 5mm
Handle S I Substrate			
No.	Item	Specification	Remark
1	Growth Method	CZ	
2	Orientation	<100>	
3	Resistivity	1-100 ohm.cm	
4	Dopant	P/B	
5	Si Thickness	675 $\pm 25\mu\text{m}$	
6	Primary flat length	47.5 ± 2 mm	
Overall Wafer Characteristics			
1	Diameter	150 ± 0.2 mm	
2	TTV	$\leq 5\mu\text{m}$	Edge exclusion 5mm
3	Bow	$\pm 50 \mu\text{m}$	Edge exclusion 5mm
4	Warp	$\leq 50\mu\text{m}$	Edge exclusion 5mm
5	Thickness	676 $\pm 25\mu\text{m}$	Edge exclusion 5mm
6	Scratches (visual inspection)	None	
7	Crack (visual inspection)	None	
Visual Defect of Backside			
1	Laser Mark	Backside	
2	Backside finish	Etched with Oxide	